

# Micro power Phase-Locked Loop

### **Features**

• Wide supply voltage range: 3.0V to 18V

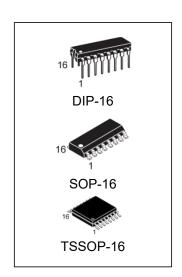
Low dynamic: 70μW (typ.) at

power consumption: fo = 10 kHz,  $V_{DD}$  = 5V

● VCO frequency: 1.3 MHz (typ.) at V<sub>DD</sub> = 10V

Low frequency drift: 0.06%/°C at V<sub>DD</sub> = 10V with temperature

• High VCO linearity: 1% (typ.)



## **Ordering Information**

DEVICE	Package Type	MARKING	Packing	Packing Qty	
CD4046BE/	DIP-16	CD4046B	TUBE	1000pcs/box	
CD4046BN	DIF-10	CD4040B	TOBE	1000pcs/box	
CD4046BM/TR	SOP-16	CD4046B	REEL	2500pcs/reel	
CD4046BMT/TR	TSSOP-16	CD4046B	REEL	2500pcs/reel	



#### **General Description**

The CD4046B micropower phase-locked loop (PLL) consists of a low power, linear, voltage-controlled oscillator (VCO), a source follower, a zener diode, and two phase comparators. The two phase comparators have a common signal input and a common comparator input. The signal input can be directly coupled for a large voltage signal, or capacitively coupled to the self-biasing amplifier at the signal input for a small voltage signal. Phase comparator I, an exclusive OR gate, provides a digital error signal (phase comp. I Out) and maintains 90° phase shifts at the VCO center frequency. Between signal input and comparator input (both at 50% duty cycle), it may lock onto the signal input frequencies that are close to harmonics of the VCO center frequency. Phase comparator II is an edge-controlled digital memory network. It provides a digital error signal (phase comp. II Out) and lock-in signal (phase pulses) to indicate a locked condition and maintains a 0° phase shift between signal input and comparator input.

The linear voltage-controlled oscillator (VCO) produces an output signal (VCO Out) whose frequency is determined by the voltage at the  $VCO_{IN}$  input, and the capacitor and resistors connected to pin  $C1_A$ ,  $C1_B$ , R1 and R2.The source follower output of the  $VCO_{IN}$  (demodulator Out) is used with an external resistor of 10 k $\Omega$  or more. The INHIBIT input, when high, disables the VCO and source follower to minimize standby power consumption. The zener diode is provided for power supply regulation, if necessary.

#### **Applications**

FM demodulator and modulator
Frequency synthesis and multiplication
Frequency discrimination
Data synchronization and conditioning
Voltage-to-frequency conversion
Tone decoding
FSK modulation
Motor speed control



## **Block & Connection Diagrams**

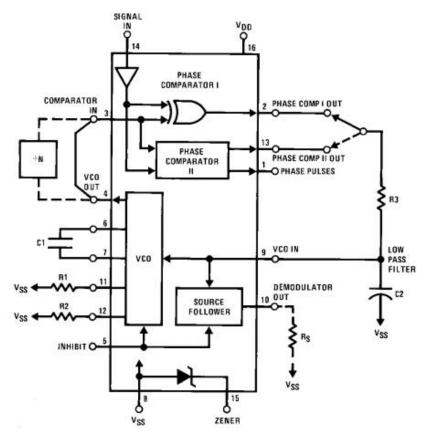
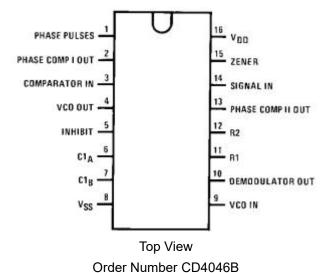


FIGURE 1

#### **Dual-In-Line Package**





# Absolute Maximum Ratings (Notes 1 & 2)

Condition	Min	Max	UNITS
DC Supply Voltage (V <sub>DD</sub> )	-0.5	+18	V
Input Voltage (V <sub>IN</sub> )	-0.5	+0.5	V
Storage Temperature Range (Ts)	-65	150	°C
Power Dissipation (P <sub>D</sub> )	-	-	-
Dual-In-Line	-	700	mW
Small Outline	-	500	mW
Lead Temperature (T <sub>L</sub> )(Soldering, 10 seconds)	-	245	°C

# **Recommended Operating Conditions (Note 2)**

Condition	Min	Max	UNITS
DC Supply Voltage (V <sub>DD</sub> )	+3	+15	V
Input Voltage (V <sub>IN</sub> )	0 to \	$J_{ m DD}$	V
Operating Temperature Range (T <sub>A</sub> )	-40	+85	°C



## DC Electrical Characteristics (Note 2)

		<u> </u>	-40	°C		+25°C		+85°C		
Symbol	Parameter	Conditions	Min	Max	Min	Тур	Max	Min	Max	Units
		Pin 5 = V <sub>DD</sub> , Pin 14 = V <sub>DD</sub> ,								
		Pin 3, 9 = V <sub>SS</sub>								
		$V_{DD} = 5V$		20		0.005	20		150	μΑ
		V <sub>DD</sub> = 10V		40		0.01	40		300	μA
	Ovices and Davice Comment	V <sub>DD</sub> = 15V		80		0.015	80		600	μΑ
I <sub>DD</sub>	Quiescent Device Current	Pin 5 = V <sub>DD</sub> , Pin 14 = Open,								
		Pin 3, 9 = V <sub>SS</sub>								
		$V_{DD} = 5V$		70		5	55		205	μA
		V <sub>DD</sub> = 10V		530		20	410		710	μΑ
		V <sub>DD</sub> = 15V		1500		50	1200		1800	μΑ
		$V_{DD} = 5V$		0.05		0	0.05		0.05	V
$V_{OL}$	Low Level Output Voltage	V <sub>DD</sub> = 10V		0.05		0	0.05		0.05	V
		V <sub>DD</sub> = 15V		0.05		0	0.05		0.05	V
		V <sub>DD</sub> = 5V	4.95		4.95	5		4.95		V
$V_{OH}$	High Level Output Voltage	V <sub>DD</sub> = 10V	9.95		9.95	10		9.95		V
		V <sub>DD</sub> = 15V	14.95		14.95	15		14.95		V
		$V_{DD} = 5V, V_{O} = 0.5V \text{ or } 4.5V$		1.5		2.25	1.5		1.5	V
VIL	Low Level Input Voltage	$V_{DD} = 10V, V_0 = 1V \text{ or } 9V$		3.0		4.5	3.0		3.0	V
	Comparator and Signal In	$V_{DD}$ = 15V, $V_{O}$ = 1.5V or 13.5V		4.0		6.25	4.0		4.0	V
		$V_{DD} = 5V, V_{O} = 0.5V \text{ or } 4.5V$	3.5		3.5	2.75		3.5		V
V <sub>IH</sub>	High Level Input Voltage	$V_{DD} = 10V, V_{O} = 1V \text{ or } 9V$	7.0		7.0	5.5		7.0		V
	Comparator and Signal In	$V_{DD} = 15V, V_0 = 1.5V \text{ or } 13.5V$	11.0		11.0	8.25		11.0		V
		$V_{DD} = 5V, V_{O} = 0.4V$	0.52		0.44	0.88		0.36		mA
$I_{OL}$	Low Level Output Current	$V_{DD} = 10V, V_{O} = 0.5V$	1.3		1.1	2.25		0.9		mA
	(Note 4)	V <sub>DD</sub> = 15V, V <sub>O</sub> = 1.5V	3.6		3.0	8.8		2.4		mA
		V <sub>DD</sub> = 5V, V <sub>O</sub> = 4.6V	-0.52		-0.44	-0.88		-0.36		mA
$I_{OH}$	High Level Output Current	$V_{DD} = 10V, V_{O} = 9.5V$	-1.3		-1.1	-2.25		-0.9		mA
	(Note 4)	$V_{DD} = 15V, V_{O} = 13.5V$	-3.6		-3.0	-8.8		-2.4		mA
		All Inputs Except Signal Input								
I <sub>IN</sub>	Input Current	$V_{DD} = 15V, V_{IN} = 0V$		-0.3		-10 <sup>-5</sup>	-0.3		-1.0	μΑ
		V <sub>DD</sub> = 15V, V <sub>IN</sub> = 15V		0.3		10 <sup>-5</sup>	0.3		1.0	μΑ
C <sub>IN</sub>	Input Capacitance	Any Input (Note 3)					7.5			pF
		fo = 10 kHz, R1 = 1 MΩ								
		$R2 = \infty$ , $VCO_{IN} = V_{DD}/2$								
$P_T$	Total Power Dissipation	$V_{DD} = 5V$				0.07				mW
		V <sub>DD</sub> = 10V				0.6				mW
Ì		V <sub>DD</sub> = 15V				2.4				mW

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Vss e 0V unless otherwise specified.

Note 3: Capacitance is guaranteed by periodic testing.

Note 4:  $I_{\text{OH}}$  and  $I_{\text{OL}}$  are tested one output at a time.



# AC Electrical Characteristics\* TA = 25°C, CL = 50 pF

Symbol	Parameter	Conditions	Min	Тур	Max	Units
		VCO SECTION				
		fo = 10 kHz, R1 = 1 MΩ				
		$R2 = \infty$ , $VCO_{IN} = V_{DD}/2$				
$I_{DD}$	Operating Current	V <sub>DD</sub> = 5V		20		μΑ
		V <sub>DD</sub> = 10V		90		μΑ
		V <sub>DD</sub> = 15V		200		μΑ
		C1 = 50 pF, R1 = 10 k $\Omega$ ,				
		$R2 = \infty$ , $VCO_{IN} = V_{DD}$				
	Maximum Operating Frequency	V <sub>DD</sub> = 5V	0.4	0.8		MHz
		V <sub>DD</sub> = 10V	0.6	1.2		MHz
		V <sub>DD</sub> = 15V	1.0	1.6		MHz
		$VCO_{IN} = 2.5V \pm 0.3V,$				
		$R1 \ge 10 \text{ k}\Omega, V_{DD} = 5V$		1		%
	Linearity	$VCOIN = 5V \pm 2.5V$				
		R1 ≥ 400 kΩ, V <sub>DD</sub> = 10V		1		%
$f_{MAX}$		$VCO_{IN} = 7.5V \pm 5V,$				
		R1 ≥ 1 MX, V <sub>DD</sub> = 15V		1		%
		%/°C∞1/f. V <sub>DD</sub>				
	Tamananatura Francisco Chabilita Na	R2 = 00				
	Temperature-Frequency Stability No Frequency Offset, f <sub>MIN</sub> = 0	$V_{DD} = 5V$		0.12 - 0.24		%/ °C
	Frequency Offset, I <sub>MIN</sub> – 0	V <sub>DD</sub> = 10V		0.04 - 0.08		%/ °C
		V <sub>DD</sub> = 15V		0.015 - 0.03		%/ °C
		$V_{DD} = 5V$		0.06 - 0.12		%/ °C
	Frequency Offset, $f_{MIN} \neq 0$	V <sub>DD</sub> = 10V		0.05 - 0.1		%/ °C
		V <sub>DD</sub> = 15V		0.03 - 0.06		%/ °C
		V <sub>DD</sub> = 5V		10 <sup>6</sup>		МΩ
VCOIN	Input Resistance	V <sub>DD</sub> = 10V		10 <sup>6</sup>		МΩ
		V <sub>DD</sub> = 15V		10 <sup>6</sup>		МΩ
		V <sub>DD</sub> = 5V		50		%
VCO	Output Duty Cycle	V <sub>DD</sub> = 10V		50		%
		V <sub>DD</sub> = 15V		50		%
		V <sub>DD</sub> = 5V		90	200	ns
t <sub>THL</sub>	VCO Output Transition Time	V <sub>DD</sub> = 10V		50	100	ns
t <sub>THL</sub>		V <sub>DD</sub> = 15V		45	80	ns

<sup>\*</sup>AC Parameters are guaranteed by DC correlated testing.



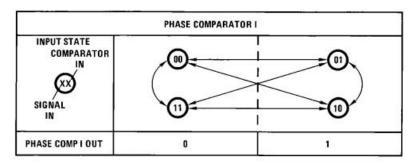
# AC Electrical Characteristics\* TA e 25°C, CL = 50 pF (Continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Units		
	PF	IASE COMPARATORS SECTION						
	Input Resistance							
	Signal Input	$V_{DD} = 5V$	1	3		МΩ		
		V <sub>DD</sub> = 10V	0.2	0.7		МΩ		
		V <sub>DD</sub> = 15V	0.1	0.3		МΩ		
	Comparator Input	$V_{DD} = 5V$		106		MΩ		
Rin		V <sub>DD</sub> = 10V		106		MΩ		
IXIN		V <sub>DD</sub> = 15V		106		МΩ		
		CSERIES = 1000 pF						
	AC-Coupled Signal Input Voltage Sensitivity	f = 50 kHz						
		$V_{DD} = 5V$		200	400	mV		
	Gensiavity	V <sub>DD</sub> = 10V		400	800	mV		
		V <sub>DD</sub> = 15V		700	1400	mV		
		DEMODULATOR OUTPUT						
		RS ≥ 10 kΩ, V <sub>DD</sub> = 5V		1.50	2.2	V		
	Offset Voltage	RS ≥ 10 kΩ, V <sub>DD</sub> = 10V		1.50	2.2	V		
VCO <sub>IN</sub> -		RS ≥ 50 kΩ, V <sub>DD</sub> = 15V		1.50	2.2	V		
VCOIN- VDEM		RS ≥ 50 kΩ						
VDLIVI	Linearity	$VCO_{IN} = 2.5V \pm 0.3V, V_{DD} = 5V$		0.1		%		
	Linearity	$VCO_{IN} = 5V \pm 2.5V, V_{DD} = 10V$		0.6		%		
		VCO <sub>IN</sub> = 7.5V±5V, V <sub>DD</sub> = 15V		0.8		%		
		ZENER DIODE			1	,		
$V_{Z}$	Zener Diode Voltage	I <sub>Z</sub> = 50 μA	6.3	7.0	7.7	V		
$R_{Z}$	Zener Dynamic Resistance	I <sub>Z</sub> = 1 mA		100		Ω		

<sup>\*</sup>AC Parameters are guaranteed by DC correlated testing.



## **Phase Comparator State Diagrams**



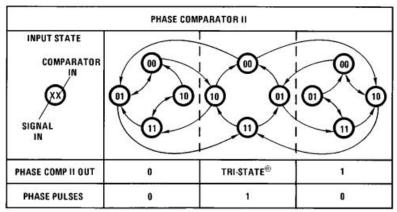


FIGURE 2

## **Typical Waveforms**

#### PHASE COMPARATORI

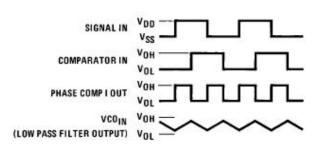


FIGURE 3. Typical Waveform Employing Phase Comparator I in Locked Condition

#### PHASE COMPARATORI

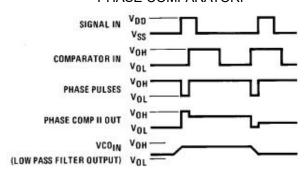
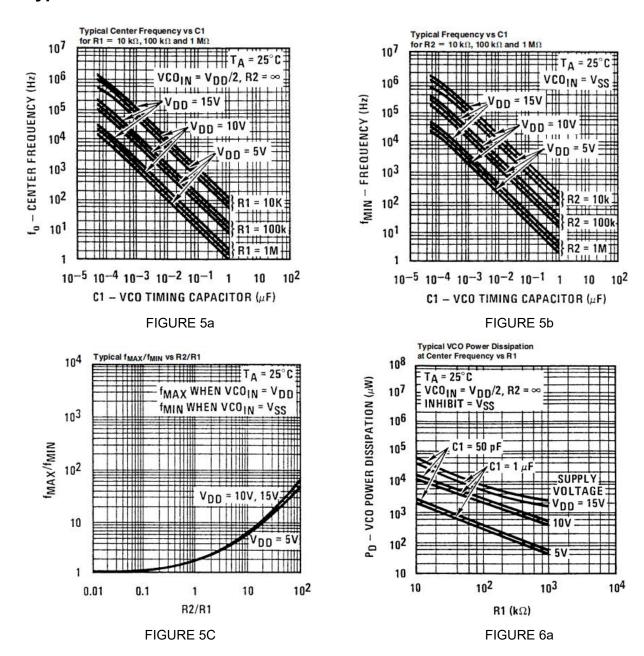


FIGURE 4. Typical Waveform Employing Phase Comparator II in Locked Condition



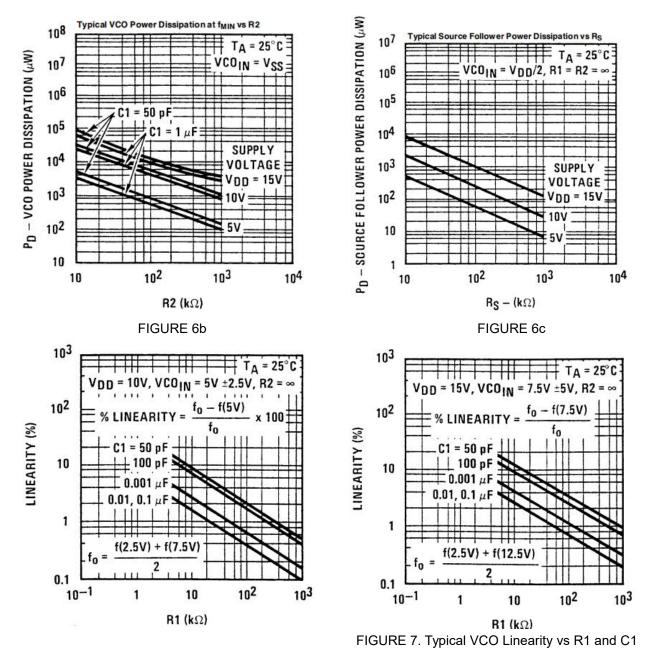
## **Typical Performance Characteristics**



Note: To obtain approximate total power dissipation of PLL system for no-signal input: Phase Comparator I, PD (Total) - PD (fo) + PD (fMIN) + PD (RS); Phas - Comparator II, PD (Total) - PD (fMIN).



## **Typical Performance Characteristics** (Continued)



Note: To obtain approximate total power dissipation of PLL system for no-signal input: Phase Comparator I, PD (Total) - PD (fo) + PD (fMIN) + PD (RS); Phase Comparator II, PD (Total) - PD (fMIN).



## **Design Information**

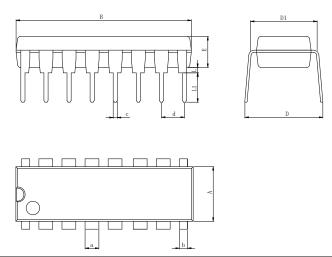
This information is a guide for approximating the value of external components for the CD4046B in a phase-lockedloop system. The selected external components must be within the following ranges: R1, R2  $\geq$  10 k $\Omega$ , RS  $\geq$  10 k $\Omega$ , C1  $\geq$  50 pF. In addition to the given design information, refer to Figure 5 for R1, R2 and C1 component selections.

		Comparator I		Comparator II
Characteristics	VCO Without Offset R2= <sup>©©</sup>	VCO With Offset	VCO Without Offset R2= <sup>©©</sup>	VCO With Offset
VCO Frequency	MAX  fo  2 fL  VDD/2 VDD  VEO INPUT VOLTAGE	f <sub>MIN</sub> V <sub>DD</sub> /2 V <sub>DD</sub> V <sub>DD</sub> V <sub>DD</sub> /2 V <sub>DD</sub>		MAX 16 16 16 17 17 17 17 17 17 17 17 17 17 17 17 17
For No Signal Input	· · · · · · · · · · · · · · · · · · ·	ystem will adjust requency, fo	_	tem will adjust to g frequency, fmin
Frequency Lock Range, 2 fL		2 fL = full VCO frequency		, ,
Frequency Capture Range, 2 fC	IN O R3 C2 C2	$2fc \approx \frac{1}{\pi} \sqrt{\frac{2\pi fL}{\pi 1}}$	fC	= fL
Loop Filter Component Selection	IN O BUT	For 2 fC, see Ref.		
Phase Angle Between Single and Comparator	_ ·	ncy (fo), approximating ls of lock range (2 fL)	Always	0° in lock
Locks on Harmonics of Center Frequency		/es	1	No
Signal Input Noise Rejection	F	ligh	L	DW
Selection	Use fo with Figure 5a to determine R1 and C1.	Calculate fmin from the equation $fmin = fo - fL.$ Use fmin with Figure 5b to determine R2 and C1. $Calculate \frac{fmax}{fmin}$ $from the equation$ $\frac{fmax}{fmin} = \frac{fo + fL.}{fo - fL}$ Use $\frac{fmax}{fmin}$ with Figure 5c to determine ratio R2/R1 to	Calculate fo from the equation $Fo = \frac{fmax}{2}$ Use fo with Figure 5a to determine R1 and C1.	Use fmin with Figure 5b to  Determine fmax fmin  Use fmax fmin with Figure 5c to determine ration  R2/R1 to obtain R1.
		obtain R1.		



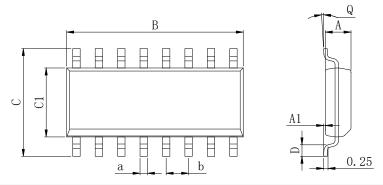
# **Physical Dimensions**

## DIP-16



Dimensions In Millimeters(DIP-16)											
Symbol:	Α	В	D	D1	E	L	L1	а	b	С	р
Min:	6.10	18.94	8.10	7.42	3.10	0.50	3.00	1.50	0.85	0.40	2.54 BSC
Max:	6.68	19.56	10.9	7.82	3.55	0.70	3.60	1.55	0.90	0.50	2.54 650

SOP-16

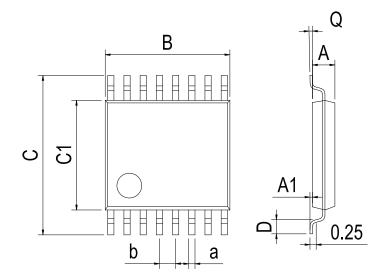


Dimensions In Millimeters(SOP-16)									
Symbol:	Α	A1	В	С	C1	D	Q	а	b
Min:	1.35	0.05	9.80	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	10.0	6.20	4.00	0.80	8°	0.45	1.21 030



# **Physical Dimensions**

## TSSOP-16



Dimensions In Millimeters(TSSOP-16)									
Symbol:	Α	A1	В	С	C1	D	Q	а	р
Min:	0.85	0.05	4.90	6.20	4.30	0.40	0°	0.20	0.65 BSC
Max:	0.95	0.20	5.10	6.60	4.50	0.80	8°	0.25	0.00 880



# **Revision History**

DATE	REVISION	PAGE
2014-6-9	New	1-15
2023-11-14	Modify the package dimension diagram TSSOP-16、Update encapsulation type、Update Lead Temperature、Updated DIP-16 dimension、Add annotation for Maximum Ratings、Update DIP Package New Model	1、4、12、13



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